

isc Silicon NPN Power Transistor

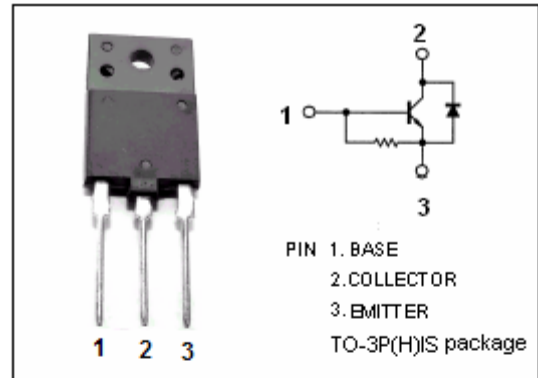
BU2520DX

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

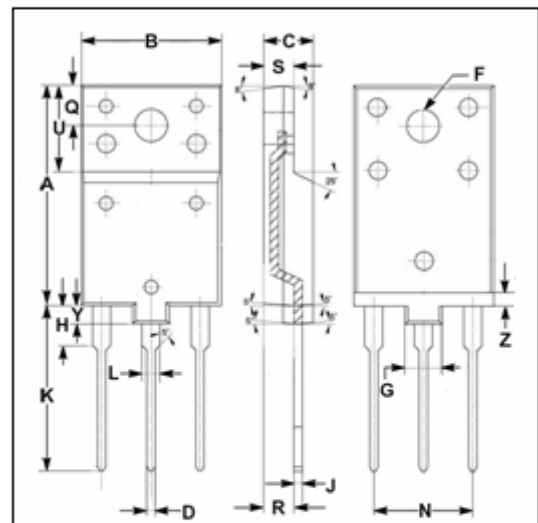
APPLICATIONS

- For use in horizontal deflection circuits of large screen colour TV receivers



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1500	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	7.5	V
I _C	Collector Current-Continuous	10	A
I _{CM}	Collector Current-peak	25	A
I _B	Base Current-Continuous	6	A
I _{BM}	Base Current-peak	9	A
P _C	Collector Power Dissipation @T _C =25°C	45	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



DIM	mm	
	MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.8	K/W

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0, L=25\text{mH}$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=600\text{mA}; I_C=0$	7.5	13.5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.1	V
I_{CES}	Collector Cutoff Current	$V_{CE}=BV_{CES}; V_{BE}=0$ $V_{CE}=BV_{CES}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$	100		300	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		13		
h_{FE-2}	DC Current Gain	$I_C=6\text{A}; V_{CE}=5\text{V}$	5	7	9.5	
V_{ECF}	C-E Diode Forward Voltage	$I_F=6\text{A}$			2.2	V
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{\text{test}}=1\text{MHz}$		115		pF

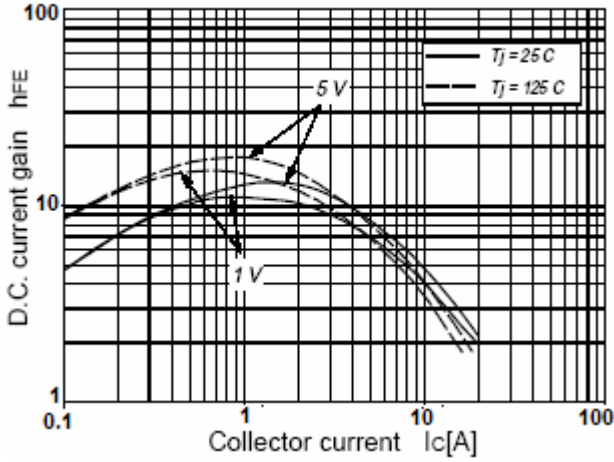
Switching times

t_{stg}	Storage Time	$I_C=6\text{A}, I_{B(\text{end})}=1.0\text{A}; L_B=5.3\mu\text{H}$ $-V_{BB}=4\text{V}; (-di_B/dt=0.8\text{A}/\mu\text{s})$			5.5	μs
t_f	Fall Time				0.5	μs

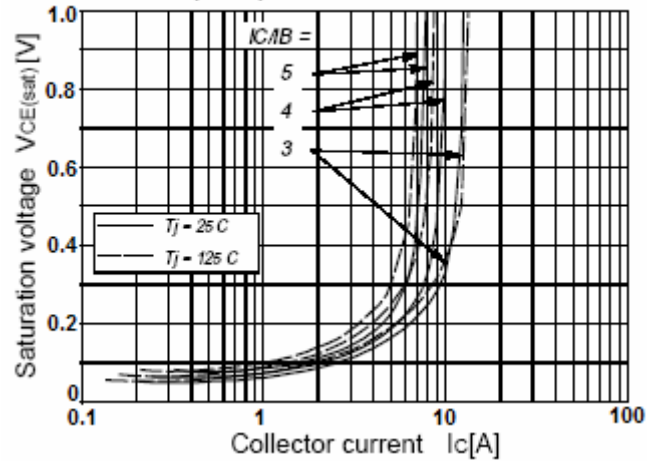
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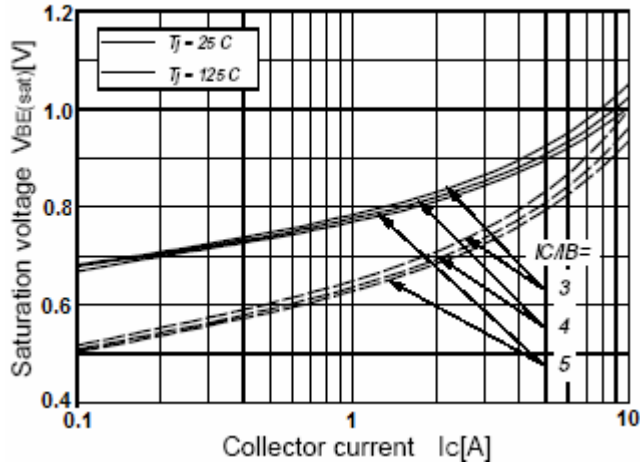
hFE-Ic Characteristics



VCE(sat)-Ic Characteristics



VBE(sat)-Ic Characteristics



Safe Operating Area

